

IN THE CLAIMS

Please cancel claims 1-8 without prejudice:

9. (Original) A method of manufacturing a bipolar transistor comprising a collector region (1) with a first doping type, and a base region (2) with a second doping type on which an emitter region (3) with a first doping type is formed, the emitter region (3) comprising a layer (6) of a first semiconductor material and a layer (7) of a second semiconductor material, characterized in that the emitter region (3) is formed by epitaxially providing a first layer (6) of the first semiconductor material, after which a second layer (7) of the second semiconductor material is subsequently epitaxially provided and doped with a first doping type such that Auger recombination occurs, and the intrinsic carrier concentration of the second semiconductor material exceeds the intrinsic carrier concentration of the first semiconductor material.

10. (Original) A method as claimed in claim 9, characterized in that the composition of the second semiconductor material on the second layer (7) is at least substantially constant.

11. (Currently Amended) A method as claimed in claim 9 ~~or 10~~, characterized in that the first semiconductor material provided comprises at least substantially silicon, and the second semiconductor material provided comprises a composition of silicon and germanium.

12. (Currently Amended) A method as claimed in claim 9, ~~10 or 11~~, characterized in that the doping provided in the second layer (7) has a doping concentration above  $3 \times 10^{20} \text{ cm}^{-3}$ .

13. (Currently Amended) A method as claimed in claim 9, ~~10 or 11~~, characterized in that the second layer (7) of the second semiconductor material is doped in situ with a first doping type during the epitaxial growth process.

14. (Currently Amended) A method as claimed in claim 9, ~~10, 11 or 12~~, characterized in that an emitter contact (10) is formed on the emitter region (3) by providing a polysilicon layer (16) with a first doping type on the emitter region (3), and the second layer (7) is doped by outdiffusion of the doping atoms from the polysilicon layer (16).

15. (Original) A method as claimed in claim 11, characterized in that the percentage of germanium in the composition is chosen to be smaller than 30%.

16. (Original) A method as claimed in claim 9, characterized in that the thickness of the second layer (7) is chosen to be above 3 nm.

17. (Currently Amended) A method of manufacturing a semiconductor device (11) comprising a semiconductor body (12) of the first semiconductor material, provided with a bipolar transistor manufactured in accordance with the method as claimed in claim 9 ~~claims 9 through 16~~.